

# Structural, Optical and Spectral Behaviour of InAs-based Quantum Dot Heterostructures

Saumya Sengupta · Subhananda Chakrabarti

# Structural, Optical and Spectral Behaviour of InAs-based Quantum Dot Heterostructures

Applications for High-performance Infrared  
Photodetectors

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# Preface

This monograph is based on research into the structural, optical and spectral properties of InAs/(In)(Al)GaAs quantum dot (QD) heterostructures, grown by using molecular beam epitaxy (MBE) with an ultimate aim to fabricate high-performance quantum dot infrared photodetectors (QDIPs).

Since the introduction of intersubband photodetectors, much attention has focused on III–V semiconductor-based, MBE-grown quantum dot (QD) heterostructures for medium- and long-wavelength infrared-imaging technology. The three-dimensional carrier confinement possible with QDs is predicted to provide better performance than available from its quantum well counterpart. We optimized various MBE growth parameters using single-layer InAs/GaAs QDs and investigated their structural, optical and spectral properties. Then, we explored the effects of growth pause or ripening time on the properties of dots. The introduction of growth pause during the growth can extend the emission wavelength of the QDs. We have also examined the effects of post-growth rapid thermal annealing (RTA) treatment on properties of single-layer QDs. The next part of the work studied InAs/GaAs bilayer QD heterostructures with very thin ( $\sim 7.5$ – $8.5$  nm) spacer layers. We have optimized minimum spacer thickness required to grow electronically coupled bilayer QD heterostructures. We have also established the superiority of bilayer QD heterostructures over the single-layer and uncoupled multilayer QD heterostructure in terms of optical and structural properties. We have examined the effects of RTA on bilayer QDs and found remarkable thermal stability of the same at high annealing temperature. Finally, we used sub-monolayer (SML) growth technique to grow QDs. This recent technique is expected to improve the electronics properties of the dots compared to those grown with the conventional Stranski–Krastanov (S-K) growth mode. After an initial study on material characterization, we established that SML QDIPs can be considered as a potential alternative to the conventional S-K QDIPs based on the comparison of the device performance.

Mumbai, India

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# Contents

<b>1</b>	<b>Introduction to Infrared Detectors and Quantum Dots</b> . . . . .	1
1.1	Introduction and Evolution of IR Detectors . . . . .	2
1.2	Introduction to Quantum Dots . . . . .	4
1.3	Motivation and Objective of the Work . . . . .	8
1.4	Conclusion . . . . .	10
	References. . . . .	10
<b>2</b>	<b>Structural, Optical and Spectral Characterization of Single-Layer QDIPs</b> . . . . .	13
2.1	Introduction . . . . .	13
2.2	Results and Discussion . . . . .	14
2.2.1	Structural Characterization . . . . .	14
2.2.2	Optical Characterization . . . . .	17
2.2.3	Spectral Characterization of Device. . . . .	20
2.3	Conclusions . . . . .	21
	References. . . . .	22
<b>3</b>	<b>Structural and Optical Characterization of Bilayer QD Heterostructures</b> . . . . .	25
3.1	Introduction . . . . .	26
3.2	Results and Discussions . . . . .	27
3.2.1	Structural Characterization . . . . .	27
3.2.2	Optical Characterization . . . . .	29
3.3	Comparison of Single-Layer, Bilayer and Multilayer QD Heterostructures . . . . .	36
3.3.1	Introduction. . . . .	36
3.3.2	Structural Characterization . . . . .	36
3.3.3	Optical Characterization . . . . .	37
3.4	Conclusions . . . . .	40
	References. . . . .	41

<b>4</b>	<b>Optical and Spectral Characterization of Sub-monolayer QDIPs . . .</b>	<b>43</b>
4.1	Introduction . . . . .	43
4.2	Optimization of the SML Heterostructure. . . . .	45
4.2.1	Results and Discussions . . . . .	46
4.3	Demonstration of High-Performance SML QDIPs . . . . .	49
4.3.1	Results and Discussions . . . . .	49
4.4	Conclusions . . . . .	56
	References. . . . .	56
<b>Index</b>	. . . . .	<b>59</b>

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# List of Figures

Fig. 1.1	Emission spectra of a blackbody at different temperatures. . . . .	2
Fig. 1.2	Atmospheric infrared-light transmissions as a function of wavelength. . . . .	3
Fig. 1.3	Schematic representation of the density-of-states for <b>a</b> bulk material, <b>b</b> 1D, <b>c</b> 2D and <b>d</b> 3D confined nanostructure. . . . .	5
Fig. 1.4	The differences between interband and intersubband energy transitions . . . . .	5
Fig. 1.5	Schematic of different growth modes of epitaxial heterostructures . . . . .	6
Fig. 1.6	Band gap and lattice constant of different semiconductors. . . . .	6
Fig. 1.7	Calculation of energy states inside an InAs/GaAs QDs heterostructure [25] . . . . .	8
Fig. 2.1	Top view SEM images of dot distributions of samples 2106 and 2109. Reprinted from “Investigation of effect of varying growth pauses on the structural and optical properties of InAs/GaAs quantum dots heterostructure” Superlattices and Microstructures, Vol. 46, No. 4, pp. 611–617, October 2009 with permission from Elsevier. . . . .	15
Fig. 2.2	STEM images of single QD grown at 0.032 ML/s with <b>a</b> 0 s and <b>b</b> 50 s of growth pause. Reprinted from “Investigation of effect of varying growth pauses on the structural and optical properties of InAs/GaAs quantum dots heterostructure” Superlattices and Microstructures, Vol. 46, No. 4, pp. 611–617, October 2009 with permission from Elsevier. . . . .	15
Fig. 2.3	STEM images of single QD grown at 0.197 ML/s with <b>a</b> 0 s and <b>b</b> 50 s of growth pause. Reprinted from “Investigation of effect of varying growth pauses on the structural and optical properties of InAs/GaAs quantum dots heterostructure” Superlattices and Microstructures, Vol. 46, No. 4, pp. 611–617, October 2009 with permission from Elsevier. . . . .	16

Fig. 2.4	PL-emission energies for samples 2106, 2105 and 2100 at 8 K. Reprinted from “Investigation of effect of varying growth pauses on the structural and optical properties of InAs/GaAs quantum dots heterostructure” Superlattices and Microstructures, Vol. 46, No. 4, pp. 611–617, October 2009 with permission from Elsevier . . . . .	17
Fig. 2.5	PL-emission energies for samples 2109, 2108 and 2115 at 8 K. Reprinted from “Investigation of effect of varying growth pauses on the structural and optical properties of InAs/GaAs quantum dots heterostructure” Superlattices and Microstructures, Vol. 46, No. 4, pp. 611–617, October 2009 with permission from Elsevier . . . . .	18
Fig. 2.6	Comparison of activation energies among the annealed counterparts of samples of all growth-pause durations. . . . .	19
Fig. 2.7	Comparison of GS PL-emission peak of as-grown sample A, B and C and their annealed counterparts . . . . .	19
Fig. 2.8	Comparison of the spectral response results of devices A and C at 50 K. . . . .	21
Fig. 3.1	Schematic diagram of the BQD heterostructure. Reprinted from, “Effect of post-growth rapid thermal annealing on bilayer InAs/GaAs quantum dot heterostructure grown with very thin spacer thickness” Materials Research Bulletin, Vol. 45, No. 11, pp. 1593–1597, November 2010 with permission from Elsevier. . . . .	27
Fig. 3.2	BFXTEM images of the InAs/GaAs BQD heterostructures— <b>a</b> 2044, <b>b</b> 2046 and <b>c</b> 2047. Reprinted from, “Vertical Ordering and Electronic Coupling in Bilayer Nanoscale InAs/GaAs Quantum Dots Separated by a Thin Spacer Layer”, Nanotechnology, Vol. 19, p. 505704, December 2008 with permission from IOP Science. © IOP Publishing. Reproduced by permission of IOP Publishing. All rights. . . . .	28
Fig. 3.3	BFXTEM images of sample A2046 <b>a</b> as-grown and annealed at <b>b</b> 700 °C and <b>c</b> 800 °C. Reprinted from, “Effect of post-growth rapid thermal annealing on bilayer InAs/GaAs quantum dot heterostructure grown with very thin spacer thickness” Materials Research Bulletin, Vol. 45, No. 11, pp. 1593–1597, November 2010 with permission from Elsevier. . . . .	30

Fig. 3.4 Low-temperature (25 K) PL spectra of the three samples measured at an incident excitation power of 5 W/cm<sup>2</sup>. Reprinted from, “Vertical Ordering and Electronic Coupling in Bilayer Nanoscale InAs/GaAs Quantum Dots Separated by a Thin Spacer Layer”, *Nanotechnology*, Vol. 19, p. 505704, December 2008 with permission from IOP Science. © IOP Publishing. Reproduced by permission of IOP Publishing. All rights . . . . . 31

Fig. 3.5 Low-temperature (25 K) PL spectra of the three samples measured at an incident excitation power of 500 W/cm<sup>2</sup>. Reprinted from, “Vertical Ordering and Electronic Coupling in Bilayer Nanoscale InAs/GaAs Quantum Dots Separated by a Thin Spacer Layer”, *Nanotechnology*, Vol. 19, p. 505704, December 2008 with permission from IOP Science. © IOP Publishing. Reproduced by permission of IOP Publishing. All rights . . . . . 31

Fig. 3.6 Low-temperature (9 K) PL spectra from sample A2044, **a** as-grown and annealed at **b** 650 and **c** 700 °C. Reprinted from, “Effect of post-growth rapid thermal annealing on bilayer InAs/GaAs quantum dot heterostructure grown with very thin spacer thickness” *Materials Research Bulletin*, Vol. 45, No. 11, pp. 1593–1597, November 2010 with permission from Elsevier. . . . . 33

Fig. 3.7 Low-temperature (9 K) PL spectra from sample A2046, as-grown and annealed at different temperatures. Reprinted from, “Effect of post-growth rapid thermal annealing on bilayer InAs/GaAs quantum dot heterostructure grown with very thin spacer thickness” *Materials Research Bulletin*, Vol. 45, No. 11, pp. 1593–1597, November 2010 with permission from Elsevier. . . . . 34

Fig. 3.8 Arrhenius plot of the temperature dependence of the integrated PL for sample A2044 both as-grown and annealed at 700 °C. Reprinted from, “Effect of post-growth rapid thermal annealing on bilayer InAs/GaAs quantum dot heterostructure grown with very thin spacer thickness” *Materials Research Bulletin*, Vol. 45, No. 11, pp. 1593–1597, November 2010 with permission from Elsevier. . . . . 35

Fig. 3.9 Arrhenius plot of the temperature dependence of the integrated PL for sample A2046, as-grown and annealed at 700 and 800 °C. Reprinted from, “Effect of post-growth rapid thermal annealing on bilayer InAs/GaAs quantum dot heterostructure grown with very thin spacer thickness” *Materials Research Bulletin*, Vol. 45, No. 11, pp. 1593–1597, November 2010 with permission from Elsevier. . . . . 35

Fig. 3.10 Three-dimensional AFM images of SQD and BQD heterostructures. Reprinted from, “Comparison of single-layer and bilayer InAs/GaAs quantum dots with a higher InAs coverage”, *Opto-Electronics Review*, Vol. 18, No. 3, pp. 295–299, September 2010 with permission from Springer . . . . . 37

Fig. 3.11 Cross-sectional TEM images of different regions of the MQD heterostructure . . . . . 38

Fig. 3.12 Comparison of SQD and BQD heterostructure PL spectra at 8 K. Reprinted from, “Comparison of single-layer and bilayer InAs/GaAs quantum dots with a higher InAs coverage”, *Opto-Electronics Review*, Vol. 18, No. 3, pp. 295–299, September 2010 with permission from Springer . . . . . 38

Fig. 3.13 Comparison of SQD and BQD heterostructure PL spectra at 300 K. Reprinted from, “Comparison of single-layer and bilayer InAs/GaAs quantum dots with a higher InAs coverage”, *Opto-Electronics Review*, Vol. 18, No. 3, pp. 295–299, September 2010 with permission from Springer . . . . . 39

Fig. 3.14 Comparison of SQD, BQD and MQD heterostructure PL spectra at 8 K . . . . . 40

Fig. 3.15 Power-dependent PL spectra MQD heterostructure at 8 K. . . . . 40

Fig. 4.1 Schematic of the S–K growth mechanism . . . . . 44

Fig. 4.2 Schematic design of the SML growth mode . . . . . 45

Fig. 4.3 Low-temperature (8 K) PL spectra of samples with varying InAs thickness. Reprinted from, “A comprehensive study on molecular beam epitaxy-grown InAs sub-monolayer quantum dots with different capping combinations”, *J. Vac. Sci. Technol. B* 31(3), 03C136-1, May/June 2013 with permission from AIP publishing LLC . . . . . 46

Fig. 4.4 Low-temperature (8 K) PL spectra with varying GaAs barrier thickness. Reprinted from, “A comprehensive study on molecular beam epitaxy-grown InAs sub-monolayer quantum dots with different capping combinations”, *J. Vac. Sci. Technol. B* 31(3), 03C136-1, May/June 2013 with permission from AIP publishing LLC . . . . . 47

Fig. 4.5 Room-temperature PL spectra of samples A, B and C. Reprinted from, “A comprehensive study on molecular beam epitaxy-grown InAs sub-monolayer quantum dots with different capping combinations”, *J. Vac. Sci. Technol. B* 31(3), 03C136-1, May/June 2013 with permission from AIP publishing LLC . . . . . 47

Fig. 4.6 Arrhenius plot from temperature-dependent PL experiments. Reprinted from, “A comprehensive study on molecular beam epitaxy-grown InAs sub-monolayer quantum dots with different capping combinations”, J. Vac. Sci. Technol. B 31 (3), 03C136-1, May/June 2013 with permission from AIP publishing LLC . . . . . 48

Fig. 4.7 Dark-current variation of devices A, B and C as a function of the applied bias voltage at 77 K. Reprinted from, “A comprehensive study on molecular beam epitaxy-grown InAs sub-monolayer quantum dots with different capping combinations”, J. Vac. Sci. Technol. B 31(3), 03C136-1, May/June 2013 with permission from AIP publishing LLC . . . . . 49

Fig. 4.8 PL spectra of device samples with a varying number of stacks at room temperature. . . . . 50

Fig. 4.9 Comparison of the PL for S–K- and SML-mode samples at room temperature. Reprinted from S. Sengupta et al., “Sub-monolayer quantum dots in confinement enhanced dots-in-a-well heterostructure”, Applied Physics Letters, Vol. 100, p. 191111, 2012 with permission from AIP publishing LLC . . . . . 50

Fig. 4.10 Comparison of normalized photocurrent spectra of QDIP devices with a varying number of stacks at 77 K. Reprinted from, “Multi-stack InAs/InGaAs sub-monolayer Quantum Dots Infrared Photodetectors”, Applied Physics Letters, Vol. 102, p. 011131, 2013 with permission from AIP publishing LLC . . . . . 51

Fig. 4.11 Detectivity as a function of the applied bias voltage for QDIP devices with a varying number of stacks at 77 K. Reprinted from, “Multi-stack InAs/InGaAs sub-monolayer Quantum Dots Infrared Photodetectors”, Applied Physics Letters, Vol. 102, p. 011131, 2013 with permission from AIP publishing LLC . . . . . 52

Fig. 4.12 Comparison of the normalized photocurrents of S–K and SML QDIPs at 77 K. Reprinted from S. Sengupta et al., “Sub-monolayer quantum dots in confinement enhanced dots-in-a-well heterostructure”, Applied Physics Letters, Vol. 100, p. 191111, 2012 with permission from AIP publishing LLC . . . . . 52

Fig. 4.13 Comparison of S–K- and SML-mode band structures. Reprinted from S. Sengupta et al., “Sub-monolayer quantum dots in confinement enhanced dots-in-a-well heterostructure”, Applied Physics Letters, Vol. 100, p. 191111, 2012 with permission from AIP publishing LLC . . . . . 53

Fig. 4.14 Dark current as a function of the applied bias voltage of QDIPs grown by S–K and SML growth modes, measured at 77 K . . . . . 54

Fig. 4.15 Detectivity as a function of the applied bias voltage for S–K and SML QDIPs at 77 K. Reprinted from S. Sengupta et al., “Sub-monolayer quantum dots in confinement enhanced dots-in-a-well heterostructure”, Applied Physics Letters, Vol. 100, p. 191111, 2012 with permission from AIP publishing LLC . . . . . 54

Fig. 4.16 Responsivity as a function of applied bias voltage of S–K and SML QDIPs at 77 K. Reprinted from S. Sengupta et al., “Sub-monolayer quantum dots in confinement enhanced dots-in-a-well heterostructure”, Applied Physics Letters, Vol. 100, p. 191111, 2012 with permission from AIP publishing LLC . . . . . 55

Fig. 4.17 Gain and absorption efficiency as a function of the applied bias voltage at 77 K for S–K and SML QDIPs. Reprinted from S. Sengupta et al., “Sub-monolayer quantum dots in confinement enhanced dots-in-a-well heterostructure”, Applied Physics Letters, Vol. 100, p. 191111, 2012 with permission from AIP publishing LLC . . . . . 55

# List of Tables

Table 1.1	Band gap and corresponding wavelengths of common semiconductors .....	4
Table 3.1	Details of different InAs/GaAs BQD heterostructure samples .....	27



# Abbreviations

0D	Zero-dimensional
1D	One-dimensional
2D	Two-dimensional
3D	Three-dimensional
A	Ampere
Å	Angstrom
AFM	Atomic force microscopy
Al	Aluminium
As	Arsenic
Au	Gold
BEP	Beam equivalent pressure
BF	Bright field
BQD	Bilayer quantum dot
CCD	Charge-coupled device
CE	Confinement enhancing
cm	Centimetre
D	Detectivity
D*	Specific detectivity
DC	Direct current
DI	De-ionized
DOS	Density of states
EM	Electromagnetic
FFT	Fast Fourier transform
FTIR	Fourier transform infrared spectroscopy
FWHM	Full width at half maximum
Ga	Gallium
Ge	Germanium
gm	Gram
G-R	Generation-recombination
HAADF	High-angle annular dark field

HgCdTe/MCT	Mercury Cadmium Telluride
HNO <sub>3</sub>	Nitric acid
H <sub>2</sub> O	Hydrogen monoxide, water
H <sub>2</sub> O <sub>2</sub>	Hydrogen peroxide
H <sub>3</sub> PO <sub>4</sub>	Phosphoric acid
HRTEM	High-resolution transmission electron microscopy
Hz	Hertz
IIT	Indian Institute of Technology
In	Indium
IPA	Isopropyl alcohol
IR	Infrared
K	Kelvin
keV	Kilo electron volt
kV	Kilo volt
LCC	Leaded chip carrier
LN <sub>2</sub>	Liquid nitrogen
LO	Longitudinal optical
LWIR	Long-wavelength infrared
MBE	Molecular beam epitaxy
MCT	Mercury Cadmium Telluride
MeV	Mega electron volt
MOCVD	Metal organic chemical vapour deposition
meV	Milli electron volt
mJ	Milli Joules
ML	Monolayer
mm	Millimetre
Mo	Molybdenum
MQD	Multilayer quantum dot
mW	Milliwatt
MWIR	Mid-wavelength infrared
μm	Micrometre
N <sub>2</sub>	Nitrogen
NEP	Noise equivalent power
Ni	Nickel
nm	Nanometre
PC	Photoconductive gain
PID	Proportion, integral and derivative
PL	Photoluminescence
PPR	Positive photoresist
QD	Quantum dot
QDIP	Quantum dot infrared photodetector
QMS	Quadrupole mass spectrometer
QW	Quantum well
QWIP	Quantum well infrared photodetectors
R	Responsivity

RHEED	Reflection high-energy electron diffraction
Sb	Antimony
Si	Silicon
S-K	Stranski–Krastanov
SML	Sub-monolayer
SNR	Signal-to-noise ratio
SQD	Single-layer quantum dot
STEM	Scanning transmission electron microscopy
TCE	Trichloroethylene
TEM	Transmission electron microscopy
TSP	Titanium sublimation pump
W	Watt
XTEM	Cross-sectional transmission electron microscopy